
2SD2651

Silicon NPN Epitaxial
High Voltage Amplifier

HITACHI

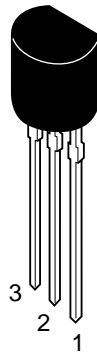
ADE-208-976 (Z)
1st. Edition
October 2000

Features

- High breakdown voltage
 $V_{CEO} = -300V$ min

Outline

TO-92 (1)



1. Emitter
2. Collector
3. Base

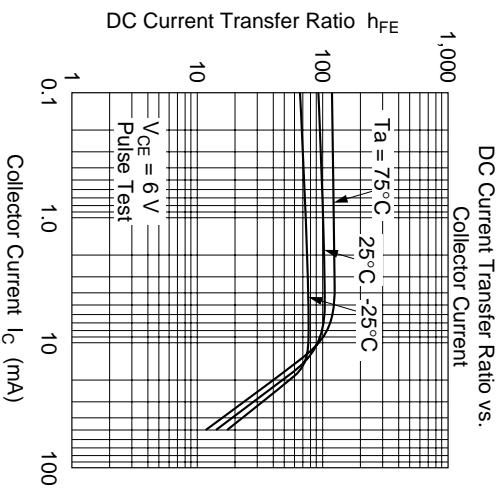
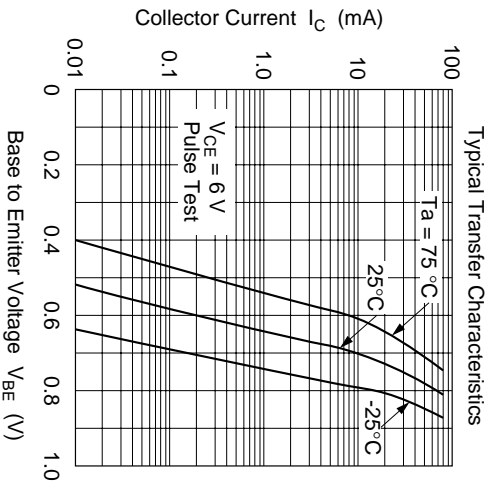
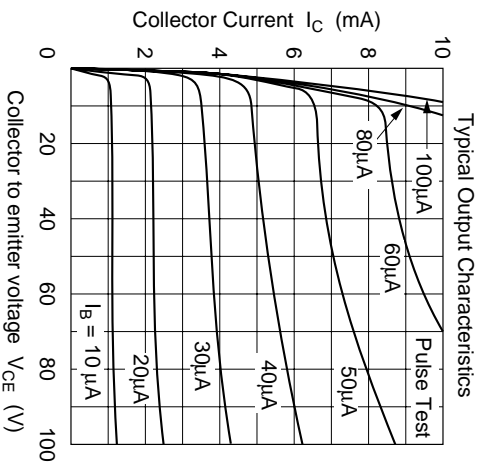
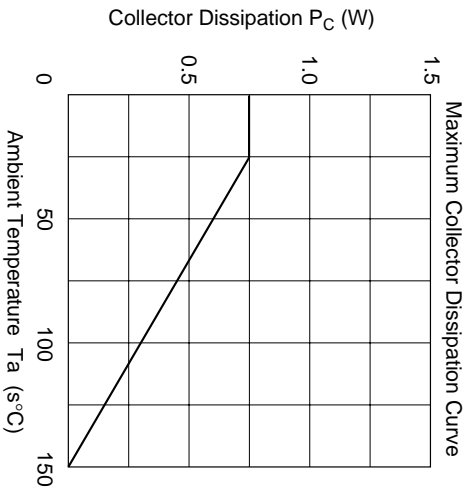
Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

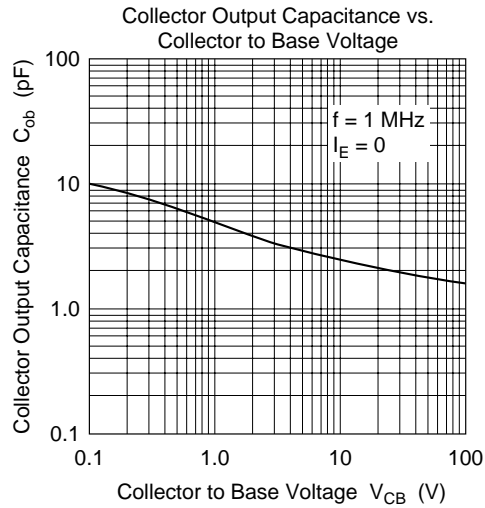
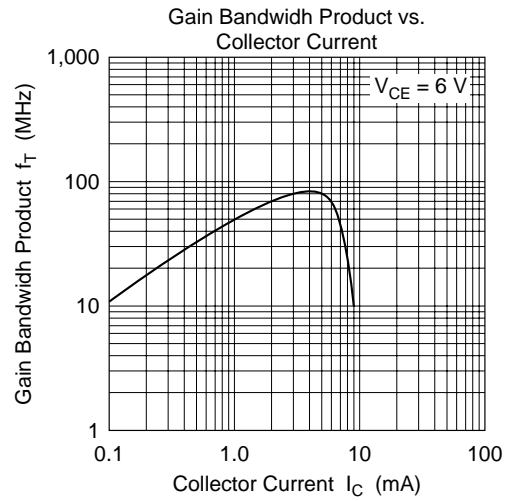
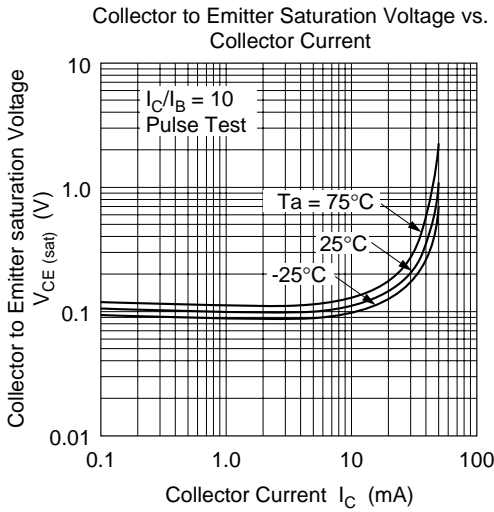
Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	300	V
Collector to emitter voltage	V_{CEO}	300	V
Emitter to base voltage	V_{EBO}	5	V
Collector current	I_{C}	50	mA
Collector power dissipation	P_{C}	750	mW
Junction temperature	T_{j}	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics ($T_a = 25^\circ\text{C}$)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Collector cutoff current	I_{CBO}	—	—	0.1	μA	$V_{\text{CB}} = 300\text{V}, I_{\text{E}} = 0$
	I_{CEO}	—	—	0.1	μA	$V_{\text{CB}} = 300\text{V}, R_{\text{BE}} = \infty$
Emitter cutoff current	I_{EBO}	—	—	10	μA	$V_{\text{EB}} = 5\text{V}, I_{\text{C}} = 0$
Base to emitter voltage	V_{BE}	—	—	0.75	V	$V_{\text{CE}} = 6\text{V}, I_{\text{C}} = 1\text{mA}$
DC current transfer ratio	h_{FE}	80	—	160	—	$V_{\text{CE}} = 6\text{V}, I_{\text{C}} = 2\text{mA}$
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	—	—	0.5	V	$I_{\text{C}} = 30\text{mA}, I_{\text{B}} = 3\text{mA}$

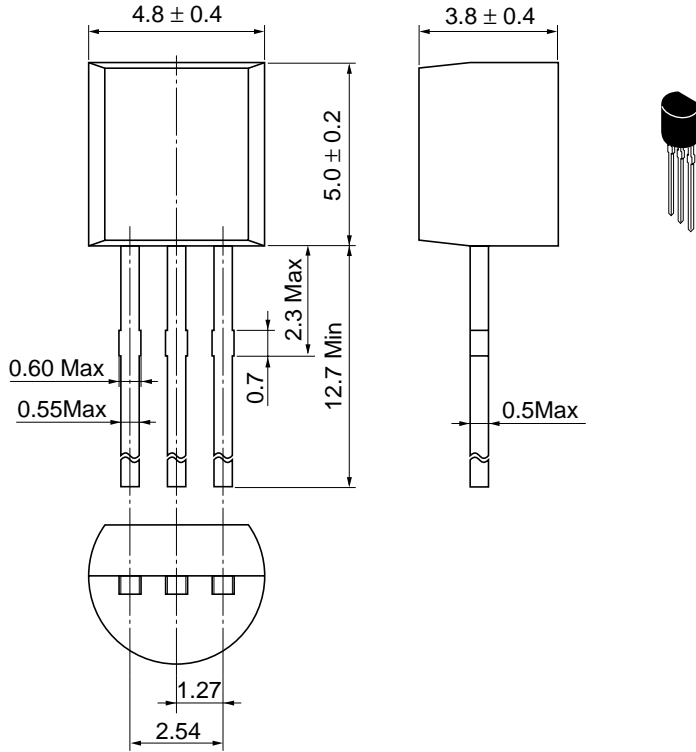
Main Characteristics





Package Dimensions

As of January, 2001
Unit: mm



Hitachi Code	TO-92 (1)
JEDEC	Conforms
EIAJ	Conforms
Mass (reference value)	0.25 g

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